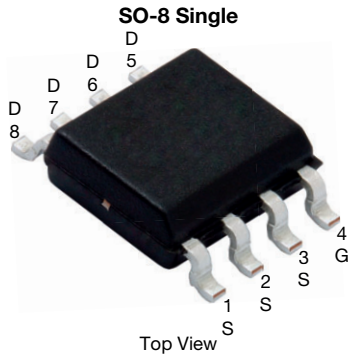


## P-Channel 30 V (D-S) MOSFET



### FEATURES

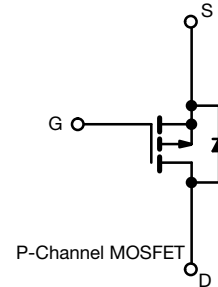
- TrenchFET® Gen III p-channel power MOSFET
- 100%  $R_g$  tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Adaptor switch
- Power management
- Load switch



PRODUCT SUMMARY	
$V_{DS}$ (V)	-30
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10$ V	0.0095
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.0150
$Q_g$ typ. (nC)	31
$I_D$ (A) <sup>a</sup>	-19.3
Configuration	Single

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	Si4153DY-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	-30	V
Gate-source voltage	$V_{GS}$	$\pm 25$	V
Continuous drain current ( $T_J = 150$ °C)	$T_C = 25$ °C	-19.3	A
	$T_C = 70$ °C	-15.4	
	$T_A = 25$ °C	-14.3 <sup>b, c</sup>	
	$T_A = 70$ °C	-11.4 <sup>b, c</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	-100	A
Continuous source-drain diode current	$T_C = 25$ °C	-5.1	A
	$T_A = 70$ °C	-3.3 <sup>b, c</sup>	
Single pulse avalanche current	$I_{AS}$	-15	A
Single pulse avalanche energy	$E_{AS}$	11.25	mJ
Maximum power dissipation	$T_C = 25$ °C	5.6	W
	$T_C = 70$ °C	3.6	
	$T_A = 25$ °C	3.1 <sup>b, c</sup>	
	$T_A = 70$ °C	2.0 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d, e</sup>		260	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b, d</sup>	$R_{thJA}$	34	40	°C/W
Maximum junction-to-case (drain)	$R_{thJF}$	18	22	

### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- Maximum under steady state conditions is 85 °C/W
- $T_C = 25$  °C



SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	-30	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$	-	-21	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	3.8	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-1	-	-2.5	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 70\text{ }^\circ\text{C}$	-	-	-15	
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -10\text{ A}$	-	0.0072	0.0095	$\Omega$
		$V_{GS} = -4.5\text{ V}$ , $I_D = -10\text{ A}$	-	0.0120	0.0150	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}$ , $I_D = -10\text{ A}$	-	44	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{DS} = -15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	-	3600	-	pF
Output capacitance	$C_{oss}$		-	430	-	
Reverse transfer capacitance	$C_{rss}$		-	390	-	
Total gate charge	$Q_g$	$V_{DS} = -15\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -10\text{ A}$	-	62	93	nC
		$V_{DS} = -15\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -10\text{ A}$	-	31	47	
Gate-source charge	$Q_{gs}$	$V_{DS} = -15\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -10\text{ A}$	-	9.2	-	-
Gate-drain charge	$Q_{gd}$		-	10.8	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.5	1.9	3.5	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$ , $R_L = 1.5\text{ }\Omega$ , $I_D \cong -10\text{ A}$ , $V_{GEN} = -4.5\text{ V}$ , $R_g = 1\text{ }\Omega$	-	50	100	ns
Rise time	$t_r$		-	46	90	
Turn-off delay time	$t_{d(off)}$		-	35	70	
Fall time	$t_f$		-	15	30	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$ , $R_L = 1.5\text{ }\Omega$ , $I_D \cong -10\text{ A}$ , $V_{GEN} = -10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	13	25	
Rise time	$t_r$		-	10	20	
Turn-off delay time	$t_{d(off)}$		-	36	70	
Fall time	$t_f$		-	10	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	-5.1	A
Pulse diode forward current	$I_{SM}$		-	-	-100	
Body diode voltage	$V_{SD}$	$I_S = -5\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-0.75	-1.1	V
Body diode reverse recovery time	$t_{rr}$	$I_F = -10\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	-	30	60	ns
Body diode reverse recovery charge	$Q_{rr}$		-	11	22	nC
Reverse recovery fall time	$t_a$		-	8	-	ns
Reverse recovery rise time	$t_b$		-	22	-	

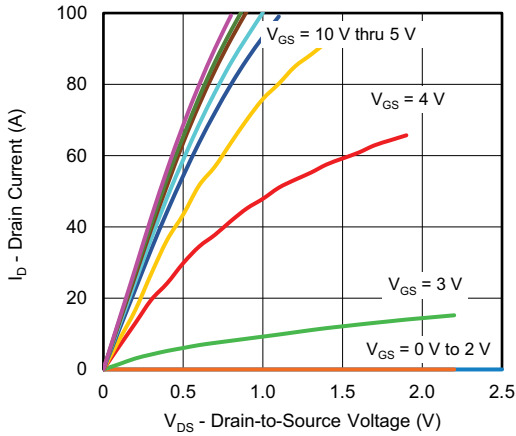
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

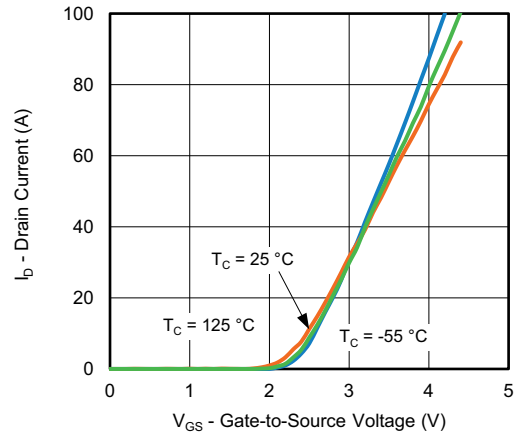
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



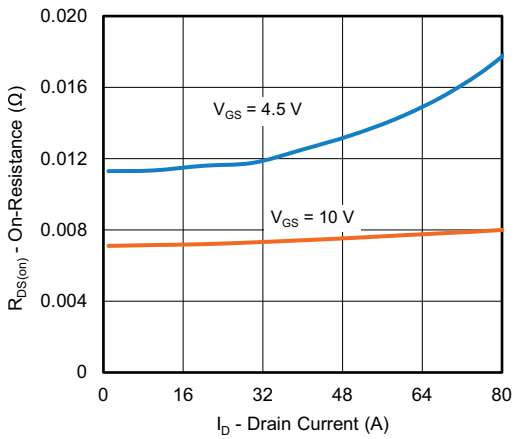
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



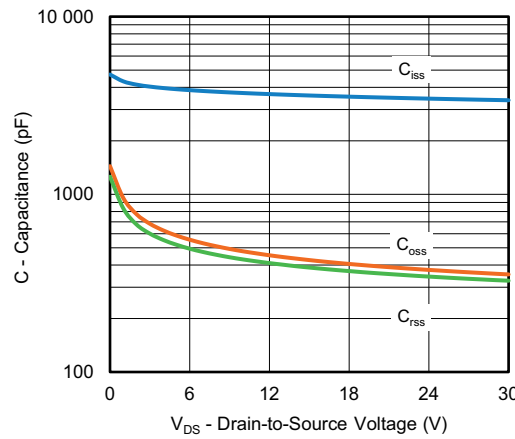
Output Characteristics



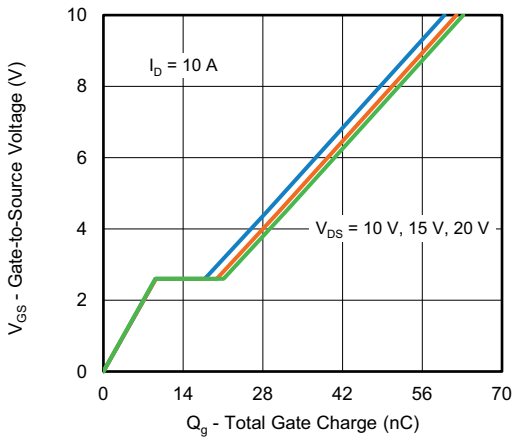
Transfer Characteristics



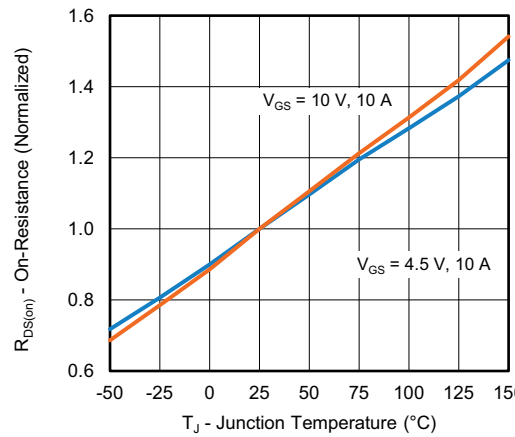
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



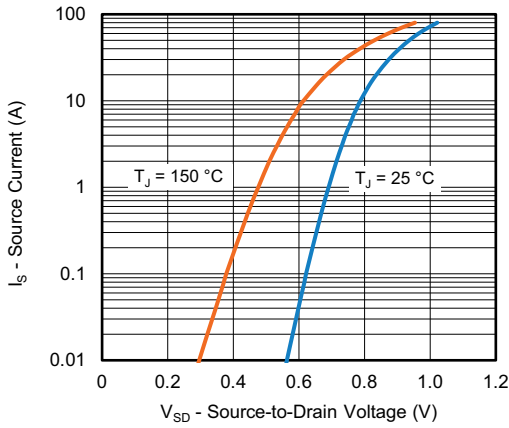
Gate Charge



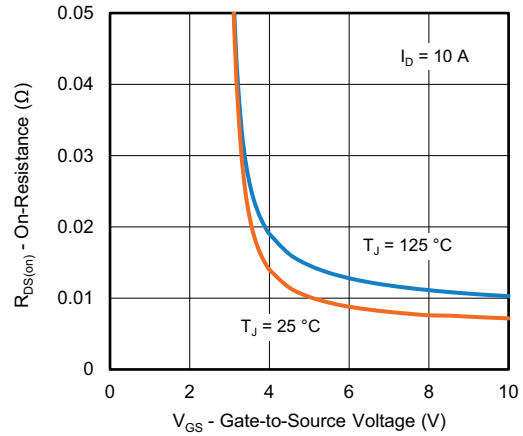
On-Resistance vs. Junction Temperature



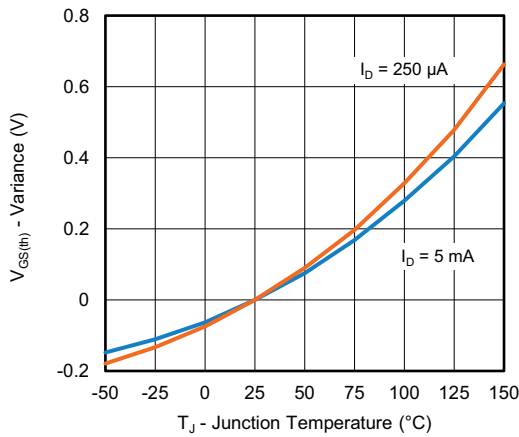
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



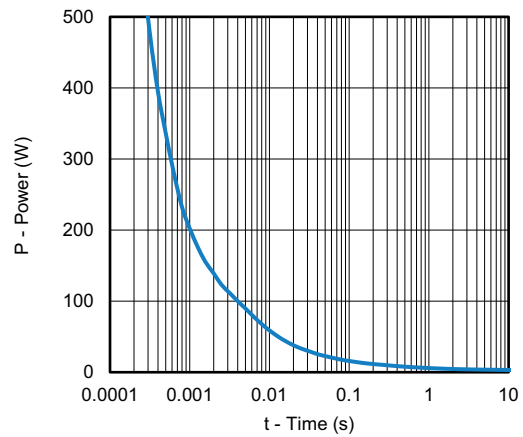
Source-Drain Diode Forward Voltage



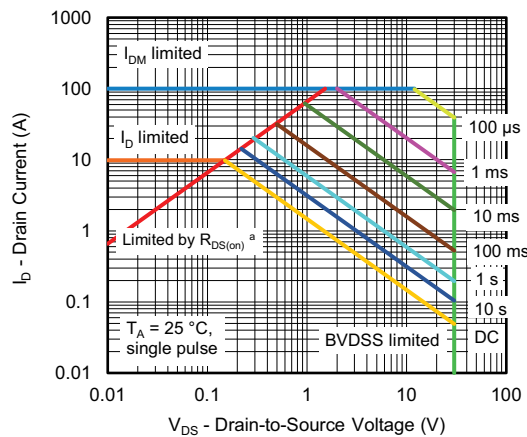
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



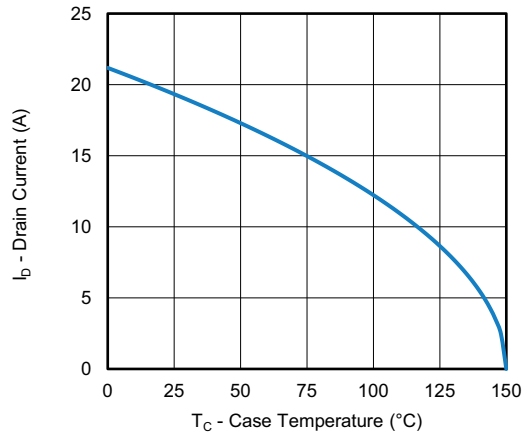
Safe Operating Area, Junction-to-Ambient

Note

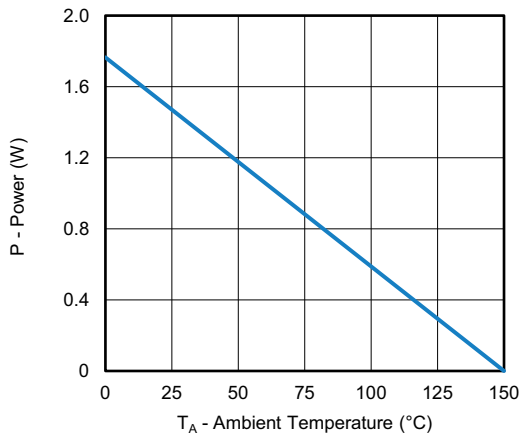
a. VGS > minimum VGS at which RDS(on) is specified



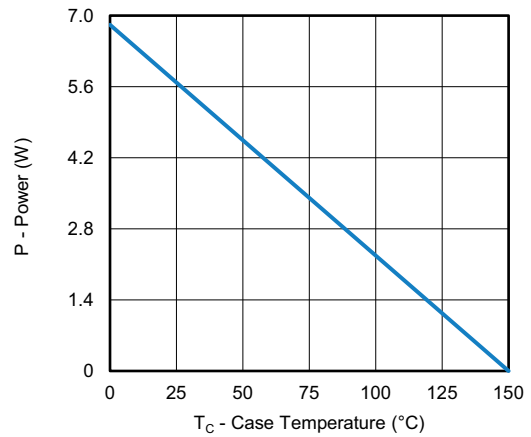
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Ambient**



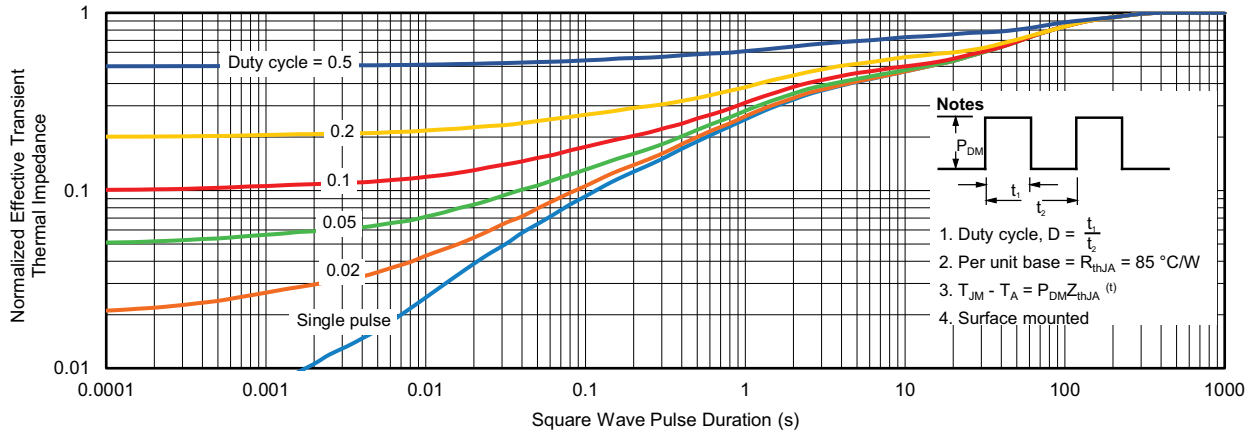
**Power, Junction-to-Case**

**Note**

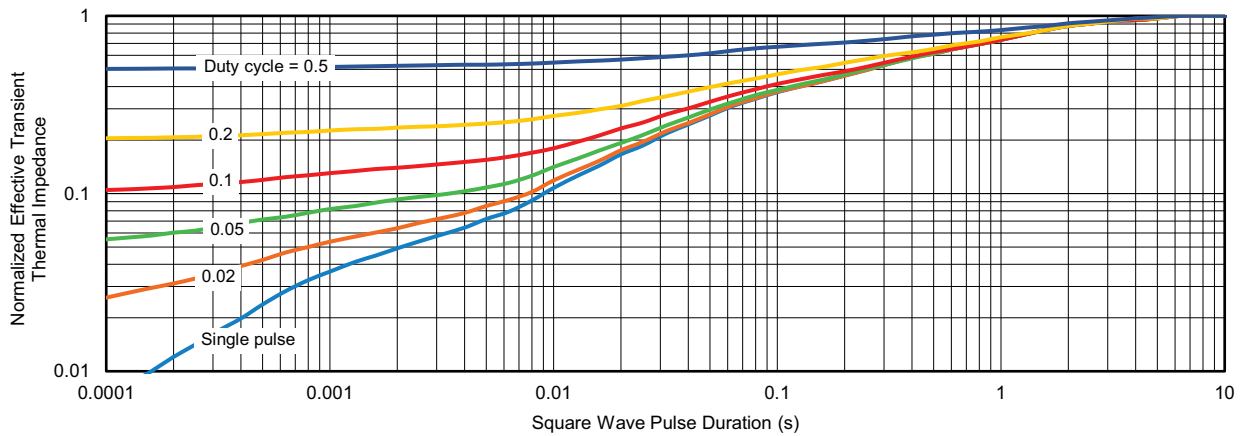
a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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